

Abstract of the Disclosure

A micro switch having a dielectric layer having a movement region formed on a substrate, a conductive layer formed on a predetermined portion of the movement region, a dielectric film formed on the conductive layer, first and second electric conductors formed a predetermined distance above the dielectric film, one or two lower electrodes formed on the movement region, and one or two upper electrodes formed a predetermined distance above the two lower electrodes, the one or two upper electrodes moving the conductive layer and the dielectric film upwards when an electrostatic force occurs between the upper and lower electrodes, and capacitively coupled with the first and second electric conductors to allow a current to flow between the first and second electric conductors. Such a micro switch has a high on/off ratio and isolation degree and a simple structure, and can be fabricated in a very easy process.